

ESD9X5V

1-Line, Uni-directional, Transient Voltage Suppressor

Descriptions

The ESD9X5V is a Uni-directional TVS (Transient Voltage Suppressor) designed to protect sensitive electronic components from damage due to ESD (Electrostatic Discharge), EFT (Electrical Fast Transients) and CDE (Cable Discharge Event). The ESD9X5V has been specifically designed to replace MLV (Multilayer Varistor) in portable application such as cellular handsets, notebook computers, tablets and PADs.

The ESD9X5V is based on solid-state silicon technology and offer unique electrical characteristics like lower clamping voltage and no device degrading compared to MLV.

The ESD9X5V may be used to provide ESD protection up to $\pm 30 kV$ (contact discharge) according to IEC61000-4-2, and withstand peak pulse current up to 11A (8/20 μ s) according to IEC61000-4-5.

The ESD9X5V is available in FBP-02C package. Standard products are Pb-free and Halogen-free.

Features

- Stand-off voltage: 5V Max.
- Transient protection for each line according to IEC61000-4-2 (ESD): ±30kV (contact discharge) IEC61000-4-5 (surge): 11A (8/20µs)
- Capacitance: C_J = 60pF typ.
- Low clamping voltage
- Solid-state silicon technology

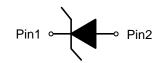
Applications

- Cellular handsets
- Tablets
- Computers and peripherals
- Notebooks
- Digital camera
- Other electronic equipment

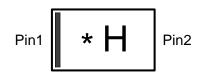
http//:www.sh-willsemi.com



FBP-02C (Bottom view)



Circuit diagram



* = Month (A~Z)
H = Device code
Marking (Top View)

Order information

Device	Package	Shipping		
ESD9X5V-2/TR	FBP-02C	10000/Tape&Reel		



Absolute maximum ratings

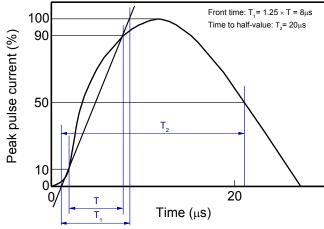
Parameter	Symbol	Rating	Unit	
Peak pulse power (t _p = 8/20µs)	P_{pk}	154	W	
Peak pulse current (t _p = 8/20µs)	I _{PP}	11	А	
ESD according to IEC61000-4-2 air discharge	V	±30	kV	
ESD according to IEC61000-4-2 contact discharge	V_{ESD}	±30		
Junction temperature	TJ	125	°C	
Operating temperature	T _{OP}	-40~85	°C	
Lead temperature	TL	260	°C	
Storage temperature	T _{STG}	-55~150	°C	

Electronics characteristics (T_A = 25°C, unless otherwise noted)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Reverse stand-off voltage	V_{RWM}				5.0	V
Reverse leakage current	I_R	$V_{RWM} = 5V$			1.0	μA
Reverse breakdown voltage	V_{BR}	$I_T = 1mA$	6.2	6.8	7.6	V
Forward voltage	V_{F}	$I_F = 1mA$	0.4	0.8	1.3	V
Clamping voltage	V _{CL}	$I_{PP} = 1A, t_p = 8/20 \mu s$			7.5	V
lamping voltage		$I_{PP} = 11A, t_p = 8/20 \mu s$			14	V
Junction capacitance	CJ	$V_R = 0V$, $f = 1MHz$		60	70	pF

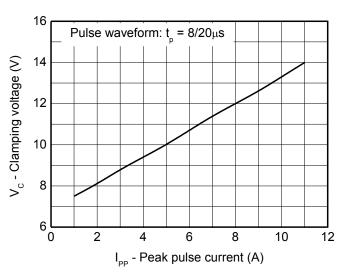


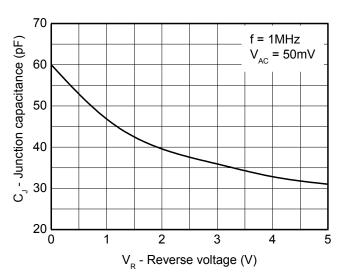
Typical characteristics (T_A = 25°C, unless otherwise noted)



100 90 10 30ns 60ns to t_r = 0.7~1ns Time (ns)

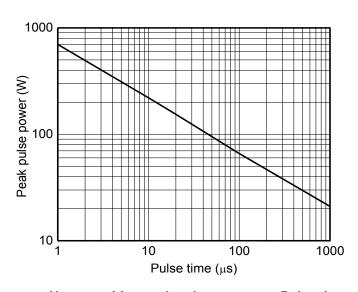
8/20µs waveform per IEC61000-4-5 Contact discharge current waveform per IEC61000-4-2

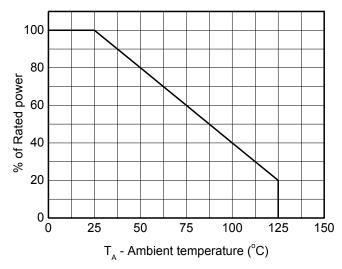




Clamping voltage vs. Peak pulse current

Capacitance vs. Reverse voltage



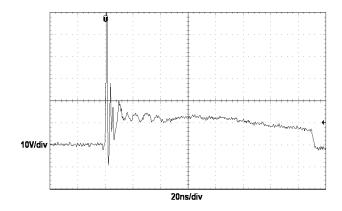


Non-repetitive peak pulse power vs. Pulse time

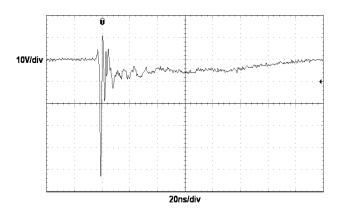
Power derating vs. Ambient temperature



Typical characteristics (T_A = 25°C, unless otherwise noted)



ESD clamping (+8kV contact discharge per IEC61000-4-2)

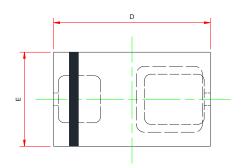


ESD clamping (-8kV contact discharge per IEC61000-4-2)

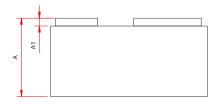


Package outline dimensions

FBP-02C

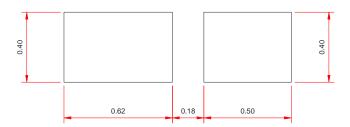


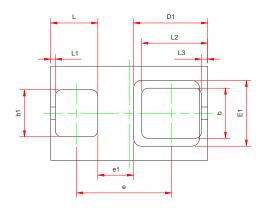
Top View



Side View

Recommend land pattern (Unit: mm)





Bottom View

O. mala al	Dimensions In Millimeters			
Symbol	Min.	Тур.	Max.	
Α	0.450	0.500	0.550	
A1	0.010		0.100	
D	0.950	1.000	1.050	
Е	0.550	0.550 0.600		
D1	0.470 Ref. 0.420 Ref.			
E1				
b	0.270	0.320	0.370	
b1	0.250	0.300	0.350	
е	0.555	0.605	0.655	
e1	0.230 Ref.			
L	0.250 0.300		0.350	
L1	0.030 Ref.			
L2	0.370	0.420	0.470	
L3	0.040 Ref.			

Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.